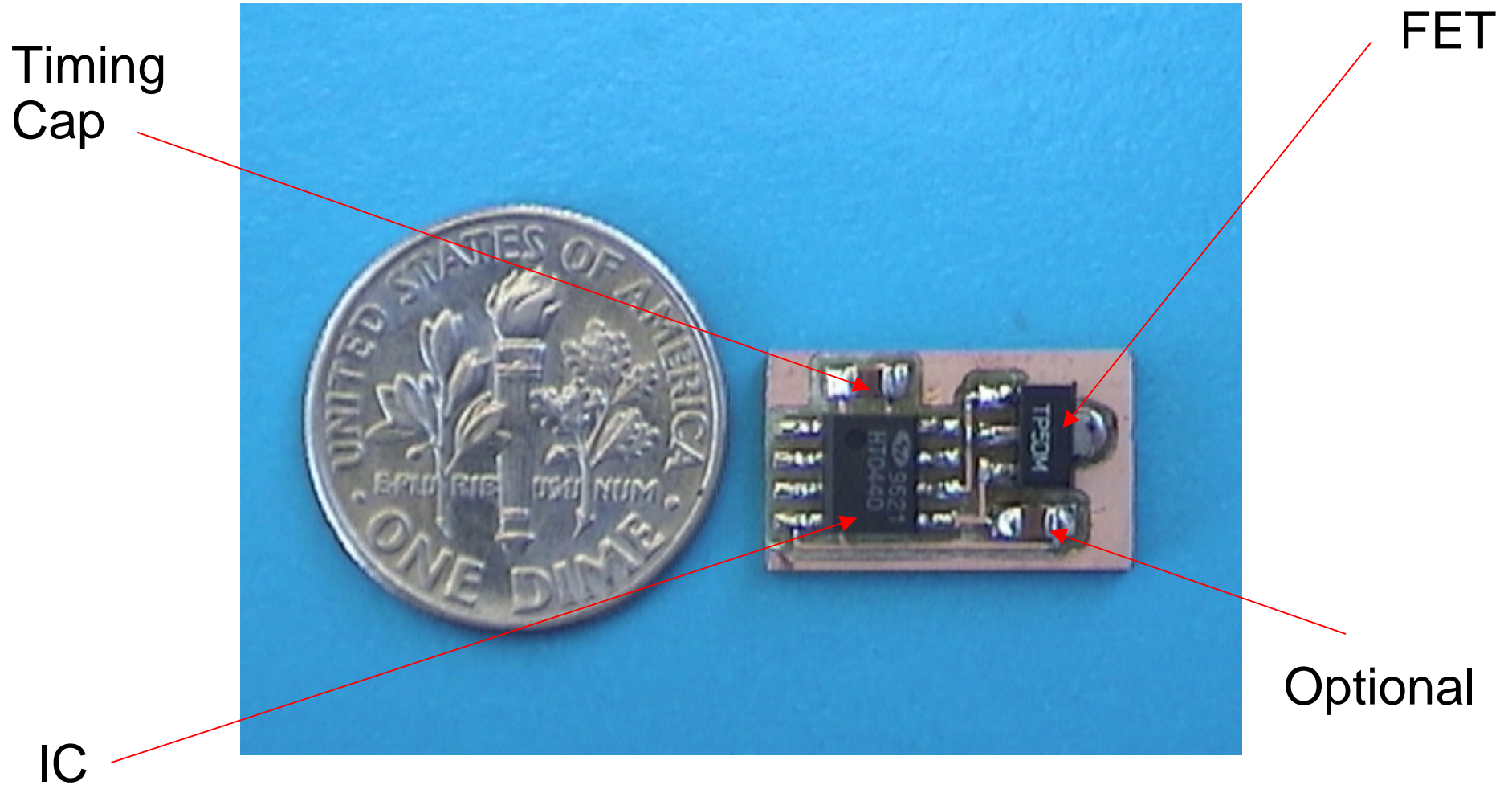
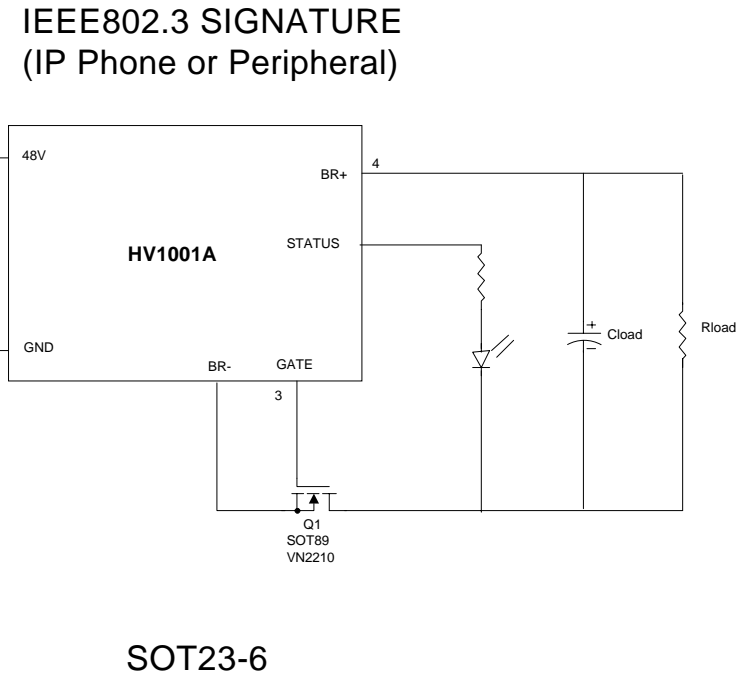
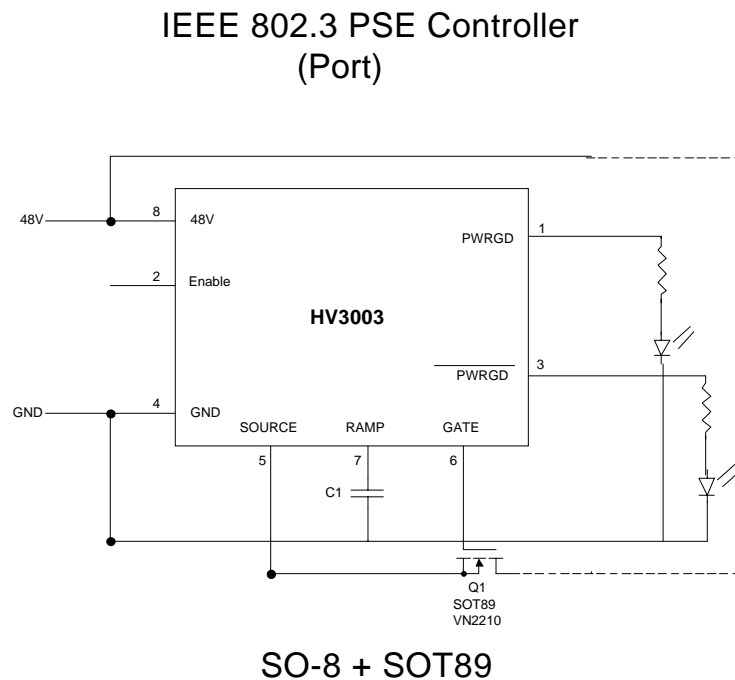


The IEEE802.3 PSE Controller and All Externals !



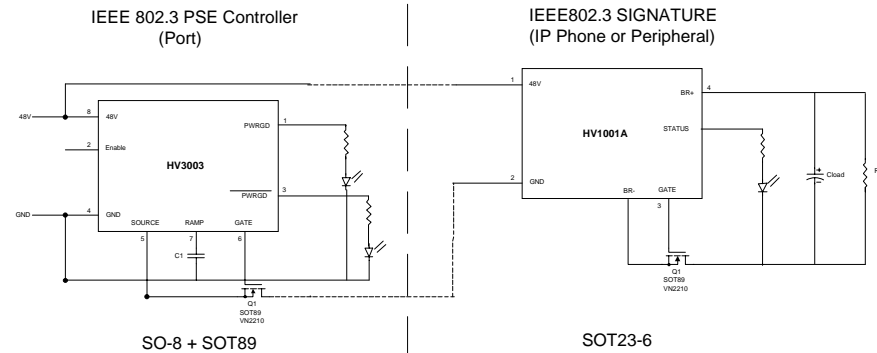
Flip Chip, uBGA & Other Package Solutions Available

An Integrated Solution



- Two External Components
- 2 Optional Components
- Enable & Optional LEDs
- Includes Signature Side A

- One External Component
- One Optional LED
- Includes Polarity Guard
- Includes Signature Side B



Considerations:

- Pass Elements Necessary on HV3003 for Power Management & Hotswap Functions
- Pass Element Necessary on HV1001A to Block Load Impedance During Signature
- UVLO/OVLO Necessary on Primary to Protect Against Input Bounce & Poor Power Conditions
- A 90V Process Required to Protect Against Overvoltages due to Lumped Network Impedances
- Current Monitoring is Implemented only in the HV3003 and not the HV1001A to Save Cost
- Tight Tolerance SiCr Resistor Required for Signature
- State Machine Polling Over a Multitude of Operating Points is Needed to Protect Against False Signature
- Long Polling Time & POR Protects Against RJ-45 Bounce
- Solution Should Have Low Quiescent Current Draw

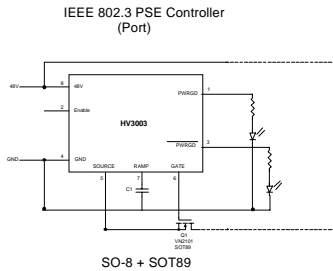
- Bounces will Reset Polling Mechanism; if somehow connection occurs pulses are 350mA & di/dt limited and 10mA < I < 700mA Circuit Breaker Will Likely Shutdown
- Ckt. Brkr. Retry Delay 100's of ms; Longer Than Bounces
- HV1001A Pass Element Must Be Off for Signature to Work; Causing Further Startup Delay After HV3003 Shutdown
- HV1001A Includes Polarity Guard
- Circuit Breaker has 10mA < I < 700mA Limits
- Persistence of 3.5us or longer Guards Against Transients
- PWRGD Delay + Extra Delay Holds off 10mA and Allows Logic Enable of the Load (Optional)
- An Enable & Two Status Outputs on HV3003 and Status on the HV1001A Allow Monitoring & Management
- Solution must be small Enough to Fit in Ports
- Solution must be Reliable (ESD) & Control EMI/RFI/Noise
- Entire System must be <\$2 with Eventual <\$1 Target



Hotswap



- Mechanical Connections “Bounce”
- High Voltage + Capacitive Load = Large Inrush
- Inrush/Ringing with Large di/dt's Can Cause EMI, RFI & Conductive Glitches/Noise, Component & Port Damage
- Signature Polling Guards Against Network Bounce
- Undervoltage & Overvoltage + POR for Primary Bounce
- Soft Start Controls Inrush - Minimizes Transients & EMI
- Circuit Breaker Protects Against Short Circuits
- Circuit Breaker has Persistence Req. & Restart Delay
- True Current Loop Control & Supertex True HV Process

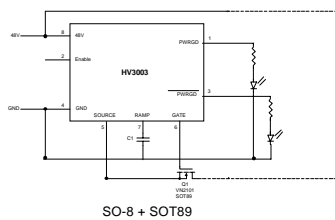


HV3003

- **Low Cost: HV3003, HV1001A, All External < \$2**
- **Intended for Primary or Mid-Span Location**
- **Lumped Inductance: Overvoltage Protection, 10V to 90V**
- **Signature on Board Incl: SiCr Resistor + Diodes**
- **SiCr Resistor has Low Temperature Variation**
- **Timing Scalable with External Ceramic Capacitor**
- **Complete Hot Swap Functionality Integral To Design**
- **EMI, RFI, Conducted Noise Friendly**
- **3kV Integral ESD Protection (up to 5kV Possible)**
- **Enable Logic Input & Two LED Regulated Outputs**
- **<1mA Active Current Draw, <400uA in Sleep Mode**
- **450mA Startup Current Limit**

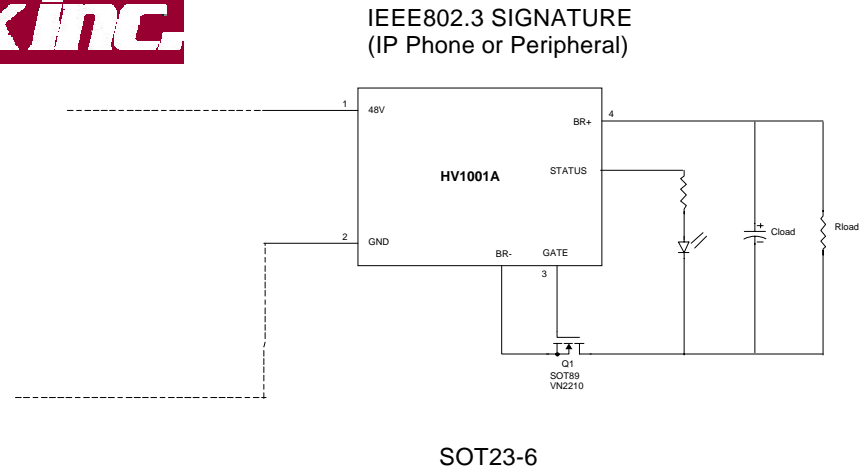


IEEE 802.3 PSE Controller
(Port)

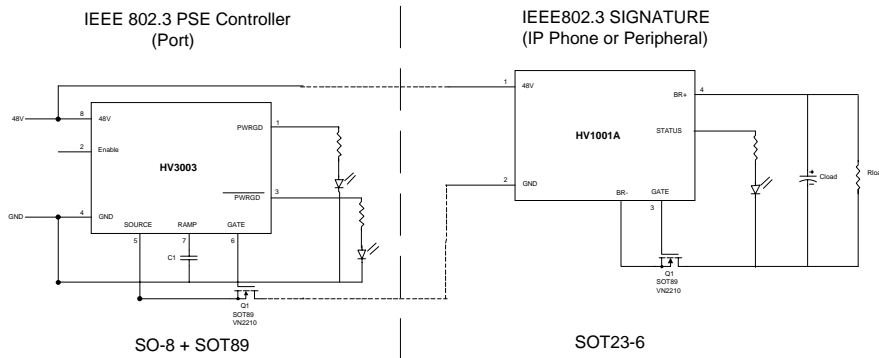


HV3003

- **Under and Overvoltage Lockout on Primary Side with Hys.**
- **Varies Current Sources to an Array of Signature Points**
- **Power On Reset Pulse**
- **10mA Circuit Breaker Holdoff Until PWRGD Goes High + Delay**
- **Slow Current Turn on over >100us**
- **Internal Voltage Regulator for Gate & Status Outputs**
- **10mA Minimum & 700mA Max. Circuit Breaker Current (Required 3.5us Persistence - can be extended)**
- **Circuit Breaker Retry After 100's of milliseconds**
- **Tiny SO-8 Footprint + SOT89 FET Saves Space**
- **Based on Advanced High Voltage Mixed Signal Process utilizing Supertex's Twenty Four Years of HV Experience**



- Intended to be Mounted in Remote IP Phone or Peripheral
- Impedance Signature on Board (SiCr + 2 Diodes of Bridge)
- Polarity Guard (Diode Bridge)
- Output Turn on Is Delayed w.r.t Input
- 3kV Integral ESD Protection (up to 5kV Possible)
- HV Comparator Sets Status Once Voltage Across FET < Threshold and Input Voltage > UVLO
- Internal Voltage Regulator for Gate & Status Output
- uPower Active Component Draw
- Pass Element Ensures Impedance Network Does Not See Load



Cases:

- RJ-45 Intact But Input Voltage on Primary Bounces
- Primary Power is Active And RJ-45 Equipment Bounces
- Removal and Re-connection of IEEE802.3 Equipment
- Remove and Re-connection of non-IEEE802.3 Equipment
- Mid-Span Insertion

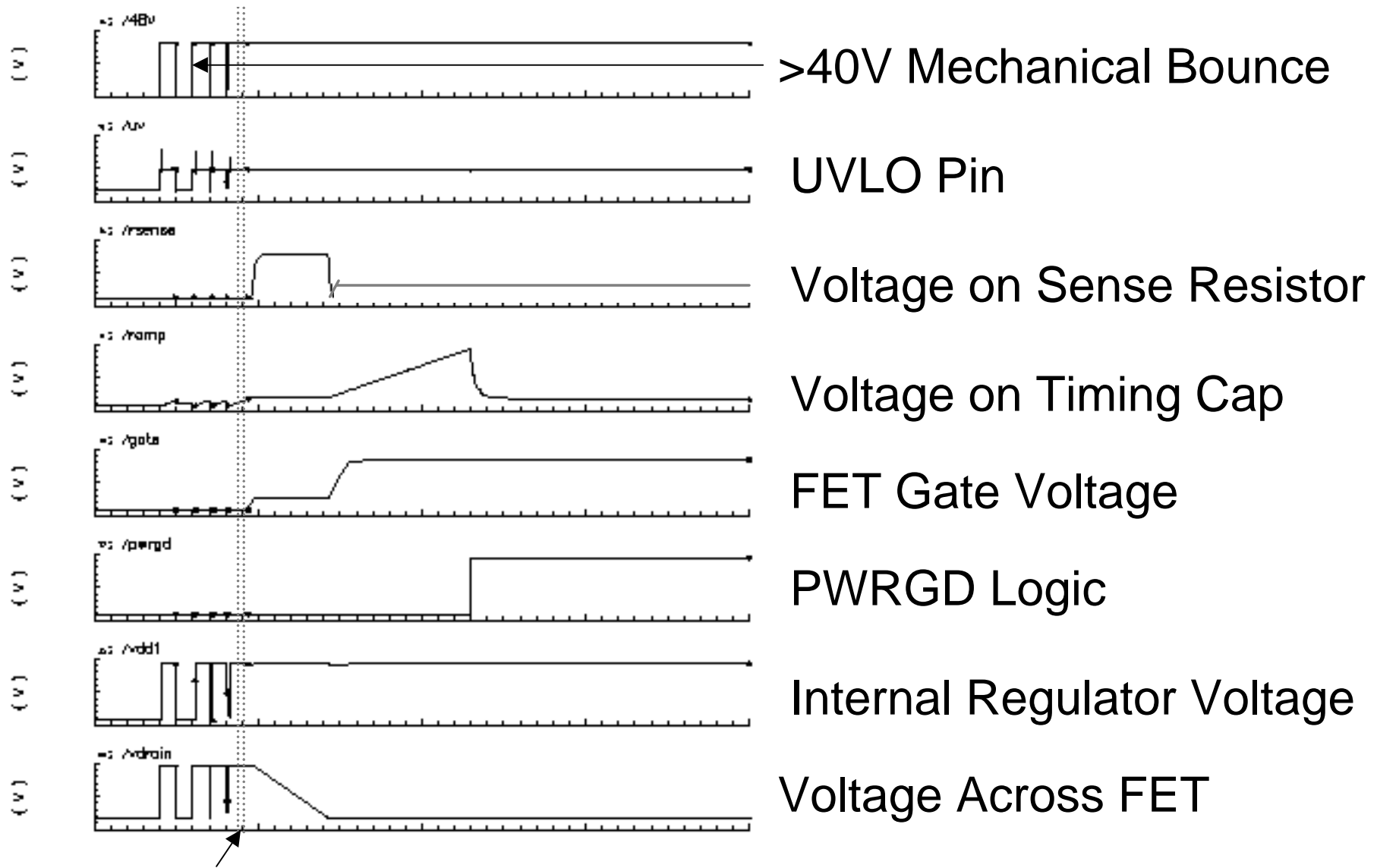
Requirements:

- Provide >40V To IEEE802.3 Device while not Causing Damage to Existing Equipment Using RJ-45
- Allowing Mid-span Insertion to Upgrade Existing Networks
- To Find a Discovery Mechanism Which Will Interoperate with Existing Equipment
- To Meet ESD, EMI, RFI & Conducted Noise/Glitch Requirements

Example Startup Sequence (Begin with HV3003):

- i) Bounce on Primary is Overcome Through UVLO/OVLO
- ii) After UVLO/OVLO POR is Followed By Signature POLL
- iii) Signature Polls for a number of milliseconds
- iv) If multiple Signature Points OK Then Continue
- v) If match incorrectly passed, then current will still have to draw between 10mA and 700mA or Ckt. Bkr. Will trip and Reset will Occur
- vi) Bounce on RJ-45 Connector will Reset Polling Mechanism. Signature cannot match until pass element completely shutoff - added RJ-45 Bounce Protection.
- vii) If Bounce does occur, pulses will have soft di/dt's and be limited to 450mA by the HV3003.
- viii) Polarity Bridge Ensures RJ-45 Connector Polarity
- ix) Begin Slow Turn on of Pass Element on HV3003
- x) Voltage on Gate of HV1001A Pass Element is a fraction of Input Voltage.
- xi) Current is Limited to 450mA by HV3003 until Current Drops (350mA IEEE802.3 I_{max} for load), then FET latches to Reduce R_{dson}- Contrast Comparator on HV3003?
- xii) HV1001A Pass Element Rises to Reg. Voltage
- xiii) PWRGD Delay, then HV3003 Goes into Sleep Mode
- xiv) I_{min} & I_{max} Circuit Breakers are Enabled
- xv) IC Monitors Current and Primary Voltage
- xvi) If Any Faults Persist for 3.5us (can be adjusted) then Auto-retry delay begins followed by a complete Reset.

Waveforms



Signature Polling / POR



Process Roadmap

<u>Technology</u>	<u>1999</u>	<u>2000</u>	<u>2001</u>	<u>2002</u>	<u>2003</u>	<u>Notes</u>
Low Voltage CMOS	0.8μ – 5.0μ	0.6μ	0.6μ	0.45μ	0.45μ	N-Well, P-Well, Twin Well
Med Voltage CMOS	2.0μ	2.0μ	1.2μ	1.2μ	1.2μ	10V – 12V
High Voltage CMOS	3.0μ – 5.0μ	2.0μ	1.2μ	1.2μ	1.2μ	2.0μ– 200V, 1.2μ– 100V
BiCMOS	3.0μ – 1.2μ	1.2μ	0.8μ	0.8μ	0.8μ	Both HV (up to 450V) & LV versions
CCD	3.0μ– 1.2μ	1.2μ	0.8μ	0.8μ	0.6μ	Large die capability
Dielectric Isolation	3.0μ	2.0μ	2.0μ	1.2μ	1.2μ	200V

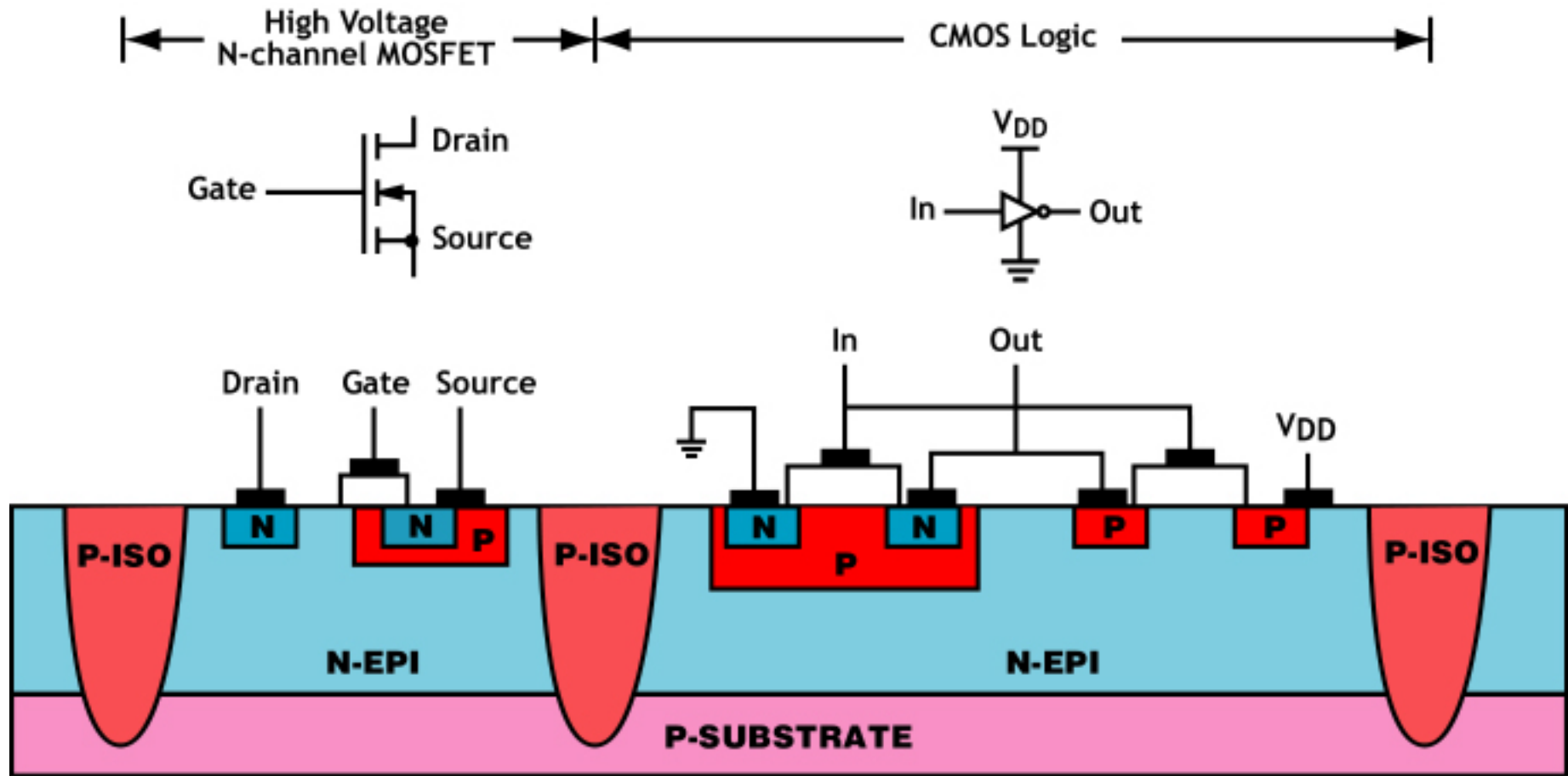
Discrete Technologies

- **Enhancement Mode DMOS**
 - N-channel 15v to 600v
 - P-channel 20v to 500v
 - Low Thresholds (as low as 1V)
- **Depletion Mode DMOS**
 - N-channel 240 to 500v
- **Lateral DMOS**
 - N-channel 16.5v to 500v
- **Small SO and SOT packages**
- **Available in die or wafer form**

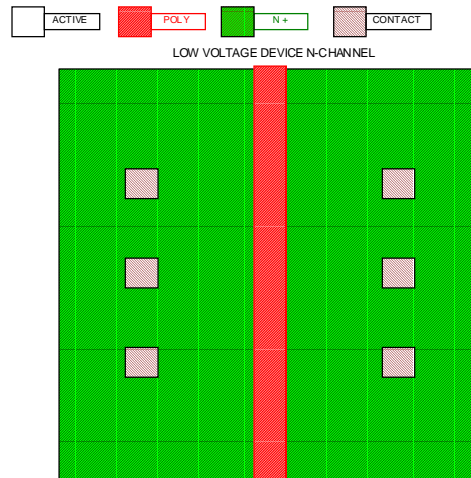
Smart Power >30 Processes

- **BiCMOS**
 - LDMOS to 450V & Depletion Devices Available
 - Integrated 120V Bipolar
 - Variety of Capacitors & Resistors
 - Zeners, Active Diodes, Zap Structures, etc.
- **SiCr Resistors**
 - Low Temperature Variation & Inside Package
- **Packaging & Trimming**
 - A Variety of Packing & Trimming Possibilities
- **Small SO and SOT packages**
- **Available in die or wafer form / Fully Packaged**

**Some Low Voltage Companies Think They Can Become HV
Overnight - But They're Years Behind !
(It's Not That Easy - Many Have Stumbled Already at 48V !)**

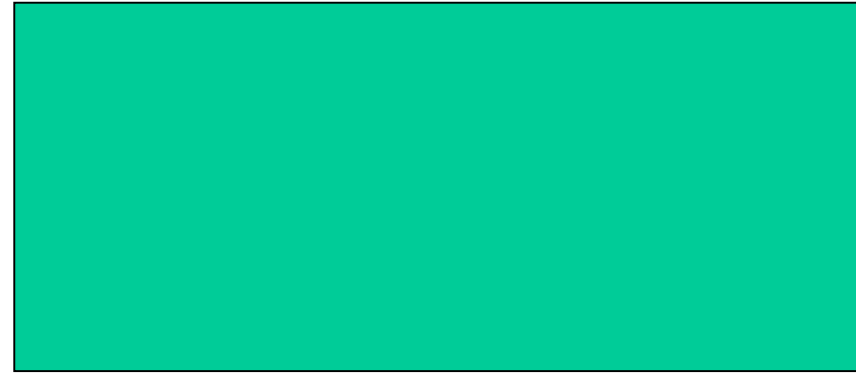


Low Voltage is Easy !



- Simple Devices
- Simple Resistors/Caps
- Latchup Easy to Avoid
- Inexpensive Tools Can Verify
- Few Devices in Library
- Few Layers
- Deep Sub-micron Geometries can Begin to Experience Effects Reminiscent of HV Designs

High Voltage Is Hard !



- Complex Well Structures with Buried Layers
- Many Complex Resistors/Cap/BJT/Diodes
- Proprietary Conductive Field Plate Materials & Knowhow with Custom Refractive Properties
- Proprietary Gate Oxide Geometries
- Many Layers
- Every Trace a Potential Latchup Candidate
- Proprietary Substrate Carrier Injection Protection
- Diffusion & Buried Layer Techniques for Wells & To Prevent Breakdown (Body Corners, etc.)
- Special Threshold Implant Control Techniques
- “Black Magic” Tricks of the Trade for Device Construction, Plate Geometries, and Reliability
- Many Devices in Library
- Very Expensive Equipment (100's of k's / seat)